

SPEC SHEET (FOR REFERENCE)	SHEET No. G05116A	Rev. 0	Page. 1 of 1
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TYPE:6PT24B3N3T * *	
CHIP SIZE	1.29 * 0.94mm
WAFER SIZE	6 inch

Maximum Ratings (Ta=25°C)

Characteristics	Symbol	Ratings	Unit
Drain-Source voltage	VDSS	30	V
Gate-Source voltage	VGSS	±20	V

WAFER PROBING SPEC (Ta=25°C)

No	MODE	LIMIT			UNIT	CONDITIONS
		MIN.	Typ	MAX.		
1	VGSS1	21	-	-	V	IG=10μA, VDS=0V
2	VGSS2	-21	-	-	V	IG=-10μA, VDS=0V
3	IGSS1	-	-	1	uA	VGS=16V, VDS=0V
4	IGSS2	-	-	-1	uA	VGS=-16V, VDS=0V
5	IGSS3	-	-	10	uA	VGS=20V, VDS=0V
6	IGSS4	-	-	-10	uA	VGS=-20V, VDS=0V
7	IDSS1	-	-	500	nA	VDS=30V, VGS=0V
8	BVDSS	32	-	-	V	ID=1mA, VGS=0V
9	Vth 1	1.2	1.6	2.0	V	ID=250uA, VGS=VDS
10	Vth 2	1.2	1.5	2.0	V	ID=0.1mA, VDS=5V
11	RDS(on)1	-	31	39	mΩ	ID=2A, VGS=10V
12	RDS(on)2	-	45	58	mΩ	ID=2A, VGS=4.5V
13	RDS(on)3	-	50	68	mΩ	ID=2A, VGS=4.0V
14	VSD	0.5	-	1.1	V	IS=100mA, VGS=0V
15	Yfs	3.0	-	-	S	VDS=5V, ID=2A

※Built in ZD between Gate and Source